

FIELD EFFECT TRANSISTOR WITH
IMPROVED ISOLATION STRUCTURES

ABSTRACT OF THE DISCLOSURE

An electronic device architecture is described comprising a field effect device in an active region 22 of a substrate 10. Channel stop implant regions 28a and
5 28b are used as isolation structures and are spaced apart from the active region 22 by extension zones 27a and 27b. The spacing is established by using an inner mask layer 20 and an outer mask layer 26 to define the isolation structures.